

Amendments to the Specification:

Please replace the paragraph starting on page 19 line 1 and ending on page 19 line 13 of the patent application as originally filed with the following amended paragraph:

A decision is then made as to whether the particle is greater than about 150 nm ~~150mm~~, in operation 706. In 130 nm technology, particles having a size greater than about 150 nm ~~mm~~ have a potential for adversely affecting the lithography process, as described previously. However, particles having a size less than about 150 nm ~~mm~~ generally will not affect the lithography process and can be ignored. Although the above description is in terms of 130 nm technology, embodiments of the present invention can also be utilized with smaller scale technology or larger scale technology. When using technology smaller than 130 nm, particles having a size less than 150 nm ~~mm~~ can affect the lithography process. As such, when using such technology a threshold value less than 150 nm ~~mm~~ can be used in operation 706. In a similar manner, a threshold value larger than 150 nm ~~mm~~ can be used in operation 706 when using larger scale technology. If the particle is greater than about 150 nm ~~150mm~~, the method 700 continues to operation 706. Otherwise, the method 700 branches to operation 708.

Please replace the paragraph starting on page 19 line 14 and ending on page 19 line 17 of the patent application as originally filed with the following amended paragraph:

In operation 708, the detected particle is ignored. As mentioned above, particles having a size less than about 150 nm ~~mm~~ generally will not affect the lithography process and can be ignored. Hence, the method 700 ignores the particle and continues with another operation 704 to detect the next backside wafer particle.

Please replace the paragraph starting on page 19 line 18 and ending on page 19 line 22 of the patent application as originally filed with the following amended paragraph:

The particle coordinates are provided to the cleaning controller, in operation 710. Particles having a size greater than about 150 nm ~~mm~~ have a potential for adversely affecting the lithography process, as described previously. Hence, embodiments of the present invention provide these coordinates to the cleaning controller, which will later direct the site-specific cleaning apparatus, as described subsequently.